M54HCT27 M74HCT27

TRIPLE 3-INPUT NOR GATE

- HIGH SPEED
 - $t_{PD} = 9 \text{ ns (TYP.)} AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 1 \mu A \text{ (MAX.)} \text{ AT } I_A = 25 \text{ °C}$
- COMPATIBLE WITH TTL OUTPUTS V_{IH} = 2V (MIN.) V_{IL} = 0.8V (MAX)
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | IOH | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS

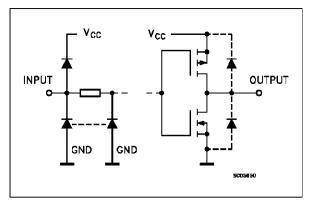
 tplh = tphl
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS27

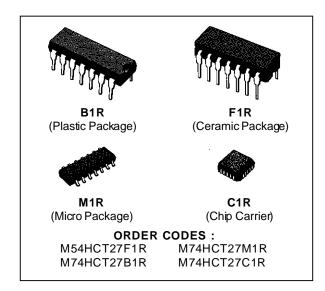
DESCRIPTION

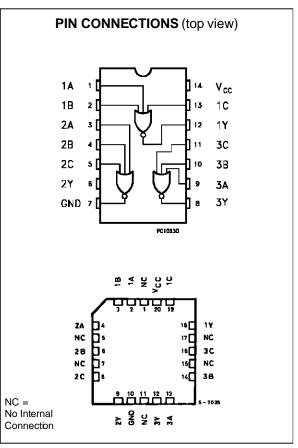
The M54/74HCT27 is a high speed CMOS TRIPLE 3-INPUT NOR GATE fabricated in silicon gate C²MOS technology.

It has the same high speed performance of LSTTL combined with true CMOS low power consumption. The internal circuit is composed of 3 stages including buffered output, which gives high noise immunity and a stable output. All inputs are equipped with protection circuits against static discharge and transient excess voltage. This integrated circuit has input and output characteristics that are fully compatible with 54/74 LSTTL logic families. M54/74HCT devices are designed to directly interface HSC²MOS systems with TTL and NMOS components. They are also plug in replacements for LSTTL devices giving a reduction of power consumption.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







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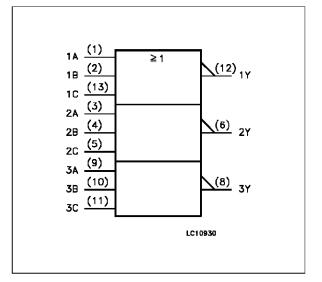
TRUTH TABLE

Α	В	С	Υ
L	_	L	Н
Н	Х	X	L
Х	Н	Х	L
Х	Х	Н	L

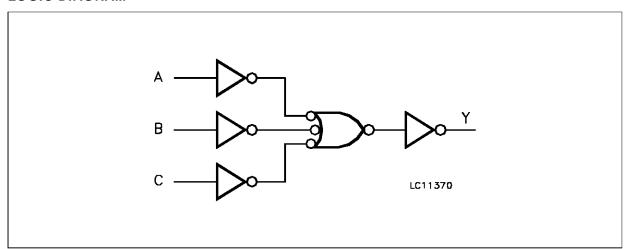
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A to 3A	Data Inputs
2, 4, 10	1B to 3B	Data Inputs
13, 5, 11	1C to 3C	Data Inputs
12, 6, 8	1Y to 3Y	Data Outputs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

IEC Logic Symbol



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \equiv 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	4.5 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V
Тор	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	ပို
t _r , t _f	Input Rise and Fall Time (V _{CC} = 4.5 to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

		Test Conditions			Value																
Symbol	Parameter	Vcc			_A = 25 ^o C and 7		-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit										
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.										
V _{IH}	High Level Input Voltage	4.5 to 5.5			2.0			2.0		2.0		V									
V _{IL}	Low Level Input Voltage	4.5 to 5.5					0.8		0.8		0.8	V									
V _{OH}	High Level Output Voltage	4.5	4.5	4.5	4.5	V _I = V _{IH}	Ι _Ο =-20 μΑ	4.4	4.5		4.4		4.4		V						
						4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5	or V _{IL}	I _O =-4.0 mA	4.18	4.31		4.13
V _{OL}	Low Level Output Voltage	4.5	V _I = V _{IH}	Ι _Ο = 20 μΑ		0.0	0.1		0.1		0.1	V									
	4.5		or V _{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.4	V									
lı	Input Leakage Current	5.5	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ									
Icc	Quiescent Supply Current	5.5	Vı = '	V _{CC} or GND			1		10		20	μΑ									
ΔΙCC	Additional worst case supply current	5.5	V _I : V Othe	Input pin = 0.5V or = 2.4V = Inputs at c or GND IO= 0			2.0		2.9		3.0	mA									

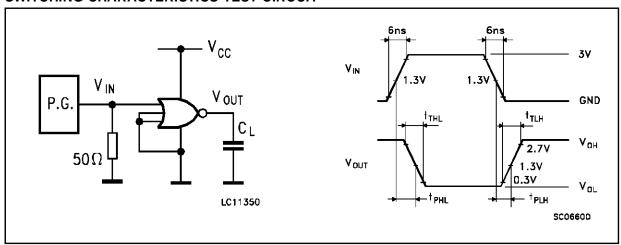


AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

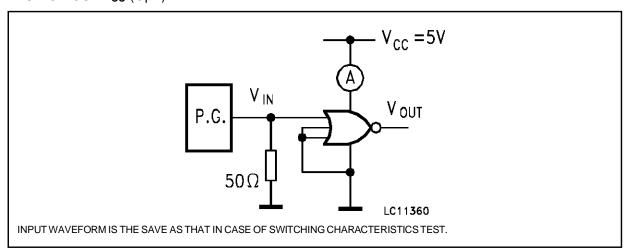
Symbol Parameter		Test Conditions		Value						
		Vcc		T _A = 25 °C -40 to 85 °C 54HC and 74HC 74HC					-55 to 125 °C 54HC	
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	4.5		8	15		19		22	ns
t _{PLH}	Propagation Delay Time	4.5		12	19		24		29	ns
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			48						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/3$ (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT

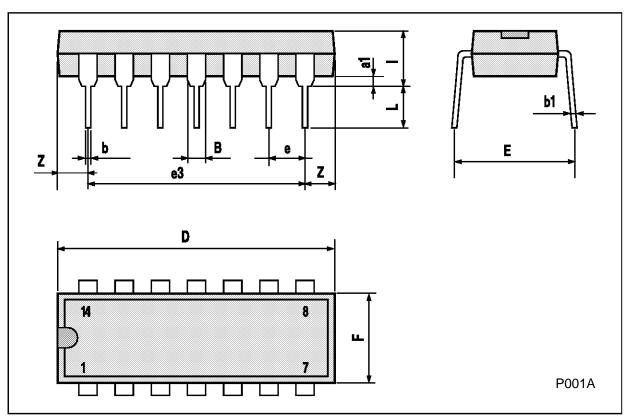


TEST CIRCUIT Icc (Opr.)



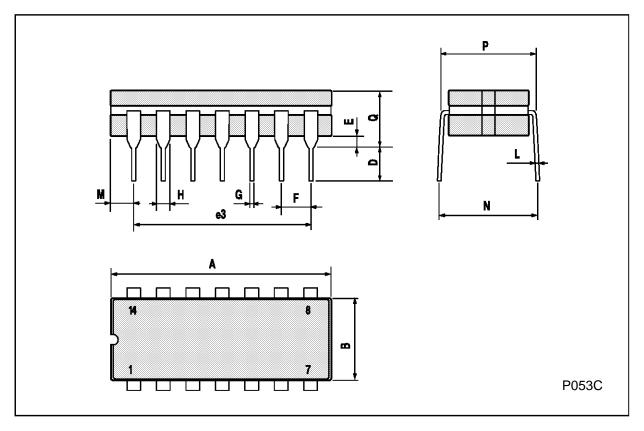
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch			
Diffi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	1.39		1.65	0.055		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		15.24			0.600		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z	1.27		2.54	0.050		0.100	



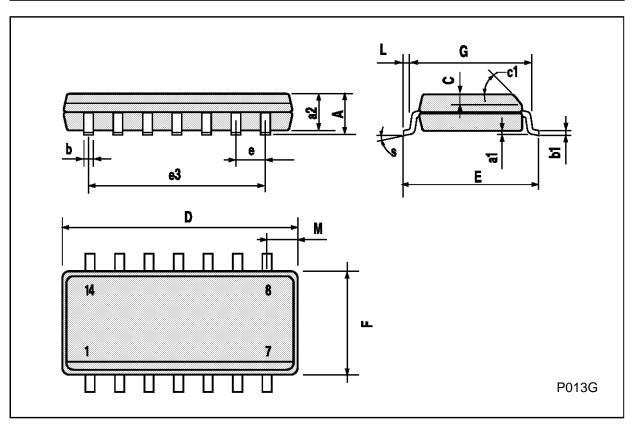
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			20			0.787	
В			7.0			0.276	
D		3.3			0.130		
E	0.38			0.015			
e3		15.24			0.600		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
M	1.52		2.54	0.060		0.100	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



SO14 MECHANICAL DATA

DIM.		mm			inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (ı	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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